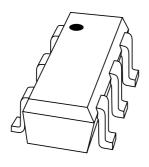
#### DISCRETE SEMICONDUCTORS

## DATA SHEET



# **PUMB9** PNP resistor-equipped double transistor; R1 = 10 kΩ, R2 = 47 kΩ

Objective specification

2003 Feb 03





## PNP resistor-equipped double transistor; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

#### PUMB9

#### **FEATURES**

- Built-in bias resistors: R1 (typ. 10 kΩ); R2 (typ. 47 kΩ)
- · Simplification of circuit design
- Reduces number of components and board space.

#### **APPLICATIONS**

- Interface circuits
- · Load driver in digital circuits.

#### **DESCRIPTION**

PNP resistor-equipped double transistor in an SC-88 (SOT363) plastic package.

#### **MARKING**

TYPE NUMBER	MARKING CODE <sup>(1)</sup>	
PUMB9	B*9	

#### Note

1. \* = p: Made in Hong Kong.

\* = t: Made in Malaysia.

#### **PINNING**

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	-50	V
I <sub>CM</sub>	peak collector current	-100	mA
TR1	PNP	_	_
TR2	PNP	_	_
R1	bias resistor	10	kΩ
R2	bias resistor	47	kΩ

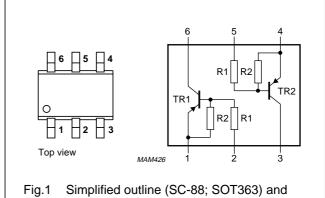
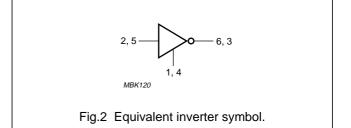


Fig.1 Simplified outline (SC-88; SOT363) and symbol.



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#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per transist	Per transistor					
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-50	V	
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-50	V	
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-10	V	
VI	input voltage					
	positive		_	+6	V	
	negative		_	-40	V	
Io	output current (DC)		_	-100	mA	
I <sub>CM</sub>	peak collector current		_	-100	mA	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	200	mW	
T <sub>stg</sub>	storage temperature		-65	+150	°C	
Tj	junction temperature		_	150	°C	
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C	
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	300	mW	

#### Note

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	416	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board, single-sided copper, tinplated and standard footprint.

<sup>1.</sup> Transistor mounted on an FR4 printed-circuit board, single-sided copper, tinplated and standard footprint.

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#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transistor						
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	_	-	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_{B} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-150	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	100	_	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	_	_	-100	mV
V <sub>i(off)</sub>	input-off voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	_	_	-0.5	V
V <sub>i(on)</sub>	input-on voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -1 \text{ mA}$	-1.4	_	_	V
R <sub>1</sub>	input resistor		7	10	13	kΩ
R2 R1	resistor ratio		3.7	4.7	5.7	
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0; V_{CB} = -10 V;$ f = 1 MHz	_	_	3	pF

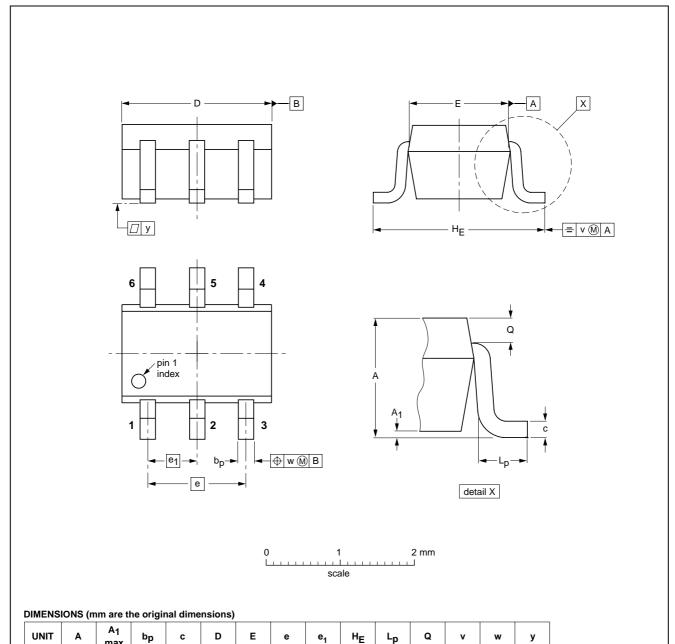
## PNP resistor-equipped double transistor; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

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#### **PACKAGE OUTLINE**

Plastic surface mounted package; 6 leads

**SOT363** 



OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION ISSUE DA	
SOT363			SC-88			97-02-28

0.65

0.25 0.15

0.2

0.2

0.1

0.45

0.15

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0.30

0.20

0.25

0.10

2.2 1.8 1.35 1.15

1.3

1.1 0.8

mm

0.1

#### PNP resistor-equipped double transistor; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

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#### **DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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**NOTES** 

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